

TQEML1223V3

TQEML1223V3

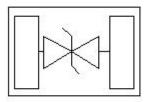
Description

The TQEML1223V3 is designed with TECH CHIP process TVS technology to protect voltage sensitive components from ESD. Excellent clamping capability, low leakage, and fast response time provide best in class protection on designs that are exposed to ESD. Because of its small size, it is suited for use in cellular phones, MP3 players, digital cameras and many other portable applications where board space comes at a premium.

• Feature

- 40W peak pulse power (tP = 8/20µs)
- DFN0603-2L Package
- Working voltage: 5V
- Low clamping voltage
- Low capacitance
- RoHS compliant transient protection for high speed data
- IEC61000-4-2(ESD)±15kV(air),±8kV(contact)

PIN configuration



DFN0603-2L

• Applications

- DVI & HDMI Port Protection
- Serial and Parallel Ports
- > Projection TV
- > Notebooks, Desktops, Servers
- High Speed Line : USB 1.0/2.0/3.0/3.1,VGA,DVI,SDI
- > Portable instrumentation

Machanical data

- Lead finish:100% matte Sn(Tin)
- Mounting position: Any
- Qualified max reflow temperature:260°C
- > Device meets MSL 1 requirements
- Pure tin plating: 7 ~ 17 um
- ➢ Pin flatness:≤3mil

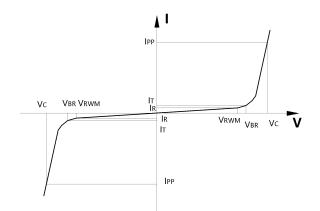
Ordering Information

Device	Package	Qty per Reel	Reel Size
TQEML1223V3	DFN0603-2L	15,000pcs	7 Inch



• Electronic Parameter

Symbol	Parameter	
V _{RWM}	Peak Reverse Working Voltage	
I _R	Reverse Leakage Current @ V _{RWM}	
V _{BR}	Breakdown Voltage @ I _T	
IT	Test Current	
I _{PP}	Maximum Reverse Peak Pulse Current	
Vc	Clamping Voltage @ I _{PP}	
P _{PP}	Peak Pulse Power	
С	Junction Capacitance	



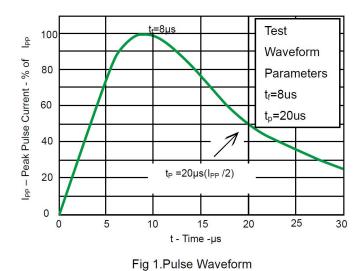
• Absolute maximum rating @TA=25°C

Symbol	Parameter	Value	Units
P _{PP}	Peak Pulse Power (8/20µS)	40	W
T _{STG}	Storage Temperature	-55/+150	°C
TJ	Operating Temperature	-55/+150	°C

• Electrical Characteristics @TA=25°C

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Peak Reverse Working	V _{RWM}			3.3		V
Voltage						
Breakdown Voltage	V _{BR}	lt = 1mA	4			V
Reverse Leakage Current	IR	VRWM =5.0V, T=25°C		0. 1		μA
Clamping Voltage	Vc	IPP = 2A, tP = 8/20µs		8.7		V
Clamping Voltage	Vc	IPP=4A, tP = 8/20µs		11	17	V
Junction Capacitance	CJ	VR=0V, f = 1MHz		7.5	15	pF

Tech Chip



• Typical Performance Characteristics

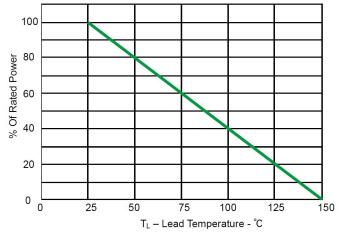
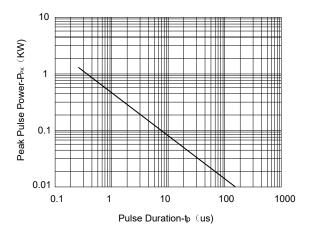


Fig 2.Power Derating Curve

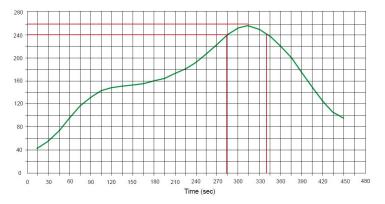


Non-Repetitive Peak Pulse Power vs. Pulse Time



• Solder Reflow Recommendation

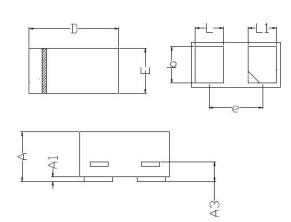
Peak Temp=257°C, Ramp Rate=0.802deg. °C/sec



• Package Information Mechanical Data

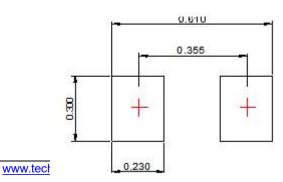
Case: DFN0603-2L

Case Material: Molded Plastic. UL Flammability



Recommended Pad outline

DIM	Millimeters		
DIN	Min	Max	
Α	0.230	0.330	
A1	0.000	0.050	
A3	0.102REF		
D	0.550	0.650	
E	0.250	0.350	
b	0.215	0.275	
L	0.115	0.175	
L1	0.115	0.175	
е	0.40BSC		



TQ-V1.1

DISCLAIMER

TECH CHIP RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN.TECH CHIPDOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICIENCE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

THE GRAPHS PROVIDED IN THIS DOCUMENT ARE STATISTICAL SUMMARIES BASED ON A LIMITED NUMBER OF SAMPLES AND ARE PROVIDED FOR INFORMATIONAL PURPOSE ONLY. THE PERFORMANCE CHARACTERISTICS LISTED IN THEM ARE NOT TESTED OR GUARANTEED. IN SOME GRAPHS, THE DATA PRESENTED MAY BE OUTSIDE THE SPECIFIED OPERATING RANGE (E.G,. OUTSIDE SPECIFIED POWER SUPPLY RANGE) AND THEREFORE OUTSIDE THE WARRANTED RANGE.